

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TH9030** is Designed for General Purpose Power oscillator Amplifier Applications up to 2.3 GHz.

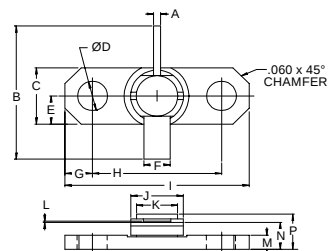
FEATURES:

- Common Collector
- Hermetic Microstrip Package
- **OmniGold™** Metalization System

MAXIMUM RATINGS

I_C	600 mA
V_{CEO}	20 V
V_{CBO}	45 V
V_{EBO}	3.0 V
P_{DISS}	7.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	25°C/W

PACKAGE STYLE .250 2L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.028 / 0.71	.032 / 0.81
B	.740 / 18.80	
C	.245 / 6.22	.255 / 6.48
D	.128 / 3.25	.132 / 3.35
E	.125 / 3.18	
F	.110 / 2.79	.117 / 2.97
G	.117 / 2.97	
H	.560 / 14.22	.570 / 14.48
I	.790 / 20.07	.810 / 20.57
J	.225 / 5.72	.235 / 5.97
K	.165 / 4.19	.185 / 4.70
L	.003 / 0.08	.007 / 0.18
M	.058 / 1.47	.068 / 1.73
N	.119 / 3.02	.135 / 3.43
P	.149 / 3.78	.187 / 4.75

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{CBO}	$V_{CB} = 30\text{ V}$			.25	mA
I_{EBO}	$V_{EB} = 2.0\text{ V}$			.25	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 100\text{ mA}$	15		120	---
C_{OB}	$V_{CB} = 20\text{ V}$ $f = 1.0\text{ MHz}$		1.5	2.5	pF
P_{Osc}	$V_{CE} = 18\text{ V}$ $I_E = 250\text{ mA}$ $f = 2.3\text{ GHz}$		1.6		W